

 Drafts

BRS: bipolar near transistor and ((variable select\$2) near (breakdown near voltage))

 Pending Active

- L1: (0) bipolar near transistor and (variable near (breakdown near voltage))
- L2: (60) bipolar near transistor and ((variable select\$2) near (breakdown near voltage))
- L3: (0) bipolar near transistor and ((variable (select\$2 near value)) near (breakdown near voltage))
- L4: (9) 2 and (emitter and sinker and collector)
- L5: (9) 2 and (emitter and base and sinker and collector)
- L6: (9) 2 and emitter and base and sinker and collector

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DBs US-PGPUB-USPAT-USOCR E Plurals

Default operator: OR

 Highlight all hit terms initially

bipolar near transistor and ((variable select\$2) near (breakdown near voltage))

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20050078848 A1	20050414	32	Power amplifier and method for split voice coil transducer or speaker	381/401	381/400; 381/402	
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20040164346 A1	20040826	7	Power switching transistor with low drain to gate capacitance	257/328	257/E29.257	
3	<input type="checkbox"/>	<input type="checkbox"/>	US 20040108547 A1	20040610	6	Power switching transistor with low drain to gate capacitance	257/335	257/E29.257	
4	<input type="checkbox"/>	<input type="checkbox"/>	US 20040009643 A1	20040115	15	METHOD FOR FABRICATING A HIGH VOLTAGE POWER MOSFET HAVING A VOLTAGE SUSTAINING REGION THAT INCLUDES DOPED COLUMNS	438/268	257/328; 257/E21.418; 257/E29.257	
5	<input type="checkbox"/>	<input type="checkbox"/>	US 20030155980 A1	20030821	6	Semiconductor device including semiconductor element of high breakdown voltage	330/311		
6	<input type="checkbox"/>	<input type="checkbox"/>	US 20030128014 A1	20030710	19	Alternator for a motor vehicle with energising information output	322/28		
7	<input type="checkbox"/>	<input type="checkbox"/>	US 20030068863 A1	20030410	13	Method for fabricating a power semiconductor device having a floating island voltage sustaining layer	438/268	257/E21.418; 257/E29.013; 257/E29.257	
8	<input type="checkbox"/>	<input type="checkbox"/>	US 20030057480 A1	20030327	8	Voltage-controlled vertical bidirectional monolithic switch	257/328	257/E29.215	
9	<input type="checkbox"/>	<input type="checkbox"/>	US 20030038680 A1	20030227	9	RF amplifier and method therefor	330/298		
10	<input type="checkbox"/>	<input type="checkbox"/>	US 20030038340 A1	20030227	17	Low-voltage punch-through bi-directional transient-voltage suppression devices and methods of making the same	257/546	257/E21.361; 257/E29.332	
11	<input type="checkbox"/>	<input type="checkbox"/>	US 20020175391 A1	20021128	17	LOW-VOLTAGE PUNCH-THROUGH BI-DIRECTIONAL TRANSIENT-VOLTAGE SUPPRESSION DEVICES AND METHODS OF MAKING THE SAME	257/497	257/361; 257/362; 257/E21.361	